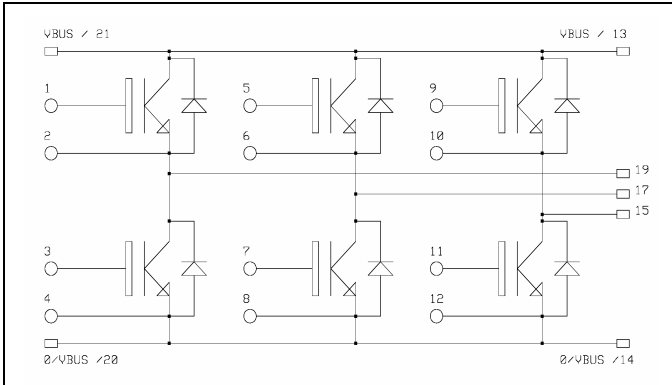


**3 Phase bridge  
Trench IGBT® Power Module**

**$V_{CES} = 1200V$   
 $I_C = 100A @ T_c = 80^\circ C$**

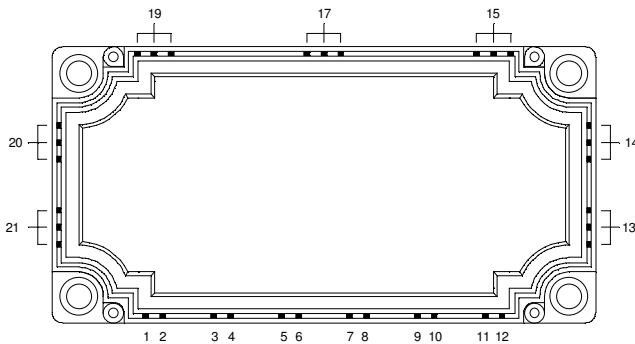


**Application**

- AC Motor control

**Features**

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration



**Benefits**

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	140
		$T_C = 80^\circ C$	100
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	280
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	480
RBSOA	Reverse Bias Operating Area	$T_j = 125^\circ C$	200A@1100V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## Electrical Characteristics

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$BV_{CES}$	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 5mA$	1200			V
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			5	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 100A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.4 2.0	1.7 2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4mA$	5.0		6.5	V
$I_{GES}$	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		7200		pF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		400		
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$		300		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ )		260		ns
$T_r$	Rise Time	$V_{GE} = \pm 15V$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$		420		
$T_f$	Fall Time	$I_C = 100A$ $R_G = 3.9\Omega$		70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ )		290		ns
$T_r$	Rise Time	$V_{GE} = \pm 15V$		45		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$		520		
$T_f$	Fall Time	$I_C = 100A$ $R_G = 3.9\Omega$		90		
$E_{off}$	Turn off Energy			12		mJ

## Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_F$	Diode Forward Voltage	$I_F = 100A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.6 1.6	2.1	V
$E_r$	Reverse Recovery Energy	$I_F = 100A$ $V_R = 600V$ $di/dt = 900A/\mu s$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	5 9		mJ
$Q_{rr}$	Reverse Recovery Charge	$I_F = 100A$ $V_R = 600V$ $di/dt = 900A/\mu s$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	10 19		$\mu\text{C}$

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
$R_{thJC}$	Junction to Case	IGBT		0.26	$^\circ\text{C/W}$	
		Diode		0.48		
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1$ min, $I_{isol} < 1mA, 50/60Hz$	2500			V	
$T_j$	Operating junction temperature range	-40		150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		125		
Torque	Mounting torque	To Heatsink	M5	3	4.5	N.m
Wt	Package Weight				300	g

